

IN THE SPECIFICATION

[0036] At step 116, the first hard mask layer 206 is removed. The cross-sectional and top plan views of the substrate 200 having the elongated features 220 (e.g., silicon elongated structures) formed on the barrier layer 202 are depicted in FIG. 2I and FIG. 2J, respectively. In one exemplary embodiment, to remove the α -carbon layer 206, step 116 may use the process described above in reference to step 106. The elongated features 220 have a distance about 110 nm or greater from one another.